

Product Summary

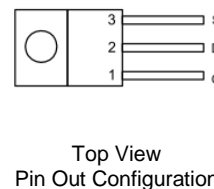
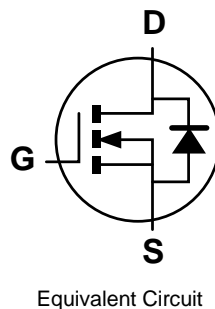
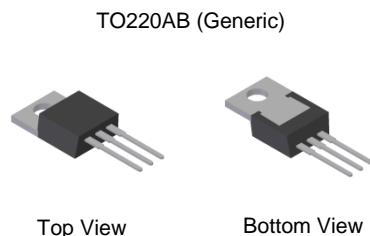
BV _{DSS}	R _{DS(ON)}	I _D T _c = +25°C
68V	8.0mΩ @ V _{GS} = 10V	100A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions



Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
 - Low Input Capacitance
 - Low Input/Output Leakage
 - **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
 - **Halogen and Antimony Free. "Green" Device (Note 3)**
 - **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**
- <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

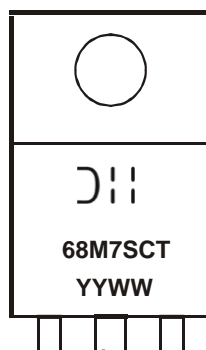
- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN68M7SCT	TO220AB (Generic)	50 Pieces/Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



= Manufacturer's Marking
 68M7SCT = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 19 = 2019)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	68	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _C = +25°C T _C = +70°C	I _D	100 80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	400	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	400	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	100	A
Avalanche Current (Note 6) L = 0.3mH			I _{AS}	35	A
Avalanche Energy (Note 6) L = 0.3mH			E _{AS}	183	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)	T _C = +25°C T _C = +70°C	P _D	125 80	W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	1.0	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	68	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 68V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6.2	8.0	mΩ	V _{GS} = 10V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	4260	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	430	—		
Reverse Transfer Capacitance	C _{rss}	—	198	—		
Gate Resistance	R _G	—	1.75	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _G	—	72.9	—	nC	V _{DD} = 30V, I _D = 20A
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	36.0	—		
Gate-Source Charge	Q _{GS}	—	8.0	—		
Gate-Drain Charge	Q _{GD}	—	15.3	—		
Turn-On Delay Time	t _{D(ON)}	—	6.3	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 1Ω, I _D = 20A
Turn-On Rise Time	t _r	—	18	—		
Turn-Off Delay Time	t _{D(OFF)}	—	36	—		
Turn-Off Fall Time	t _f	—	9.7	—		
Reverse Recovery Time	t _{RR}	—	31.4	—	ns	I _F = 20A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	30.1	—	nC	

- Notes:
- Device mounted on infinite heatsink.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

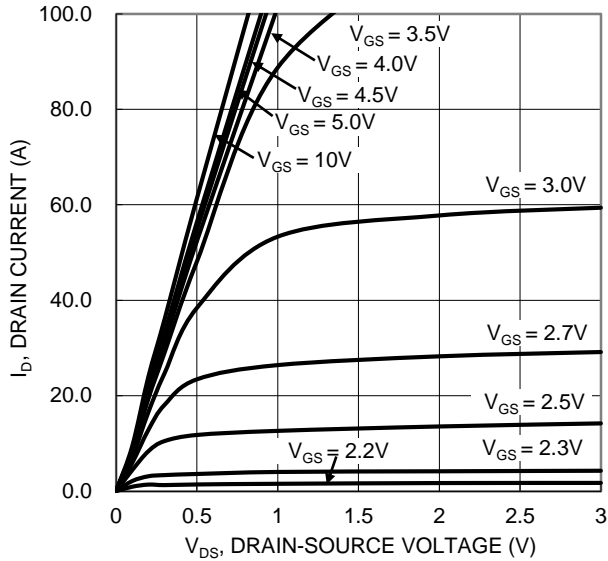


Figure 1. Typical Output Characteristic

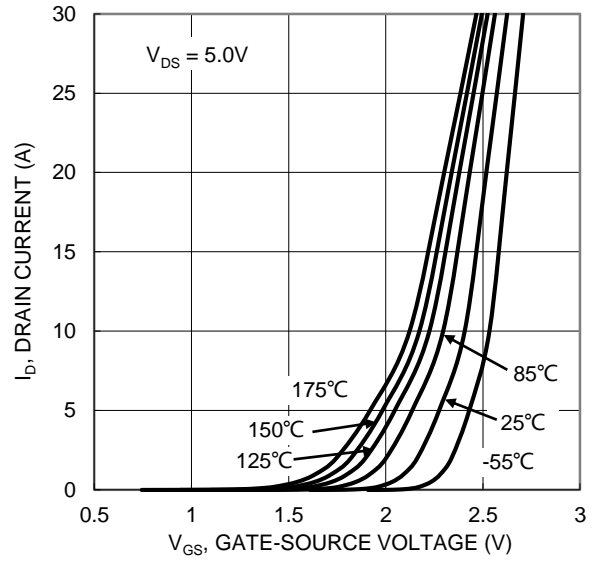


Figure 2. Typical Transfer Characteristic

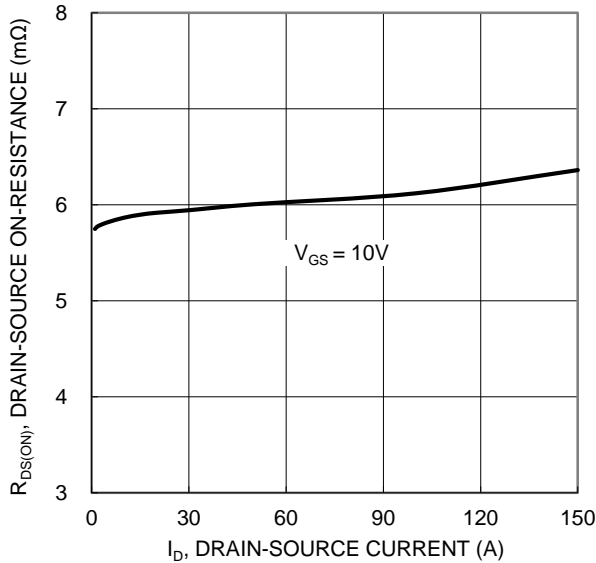


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

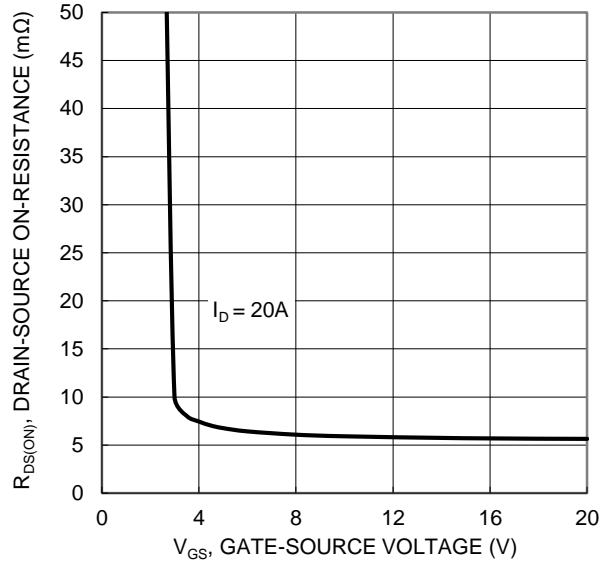


Figure 4. Typical Transfer Characteristic

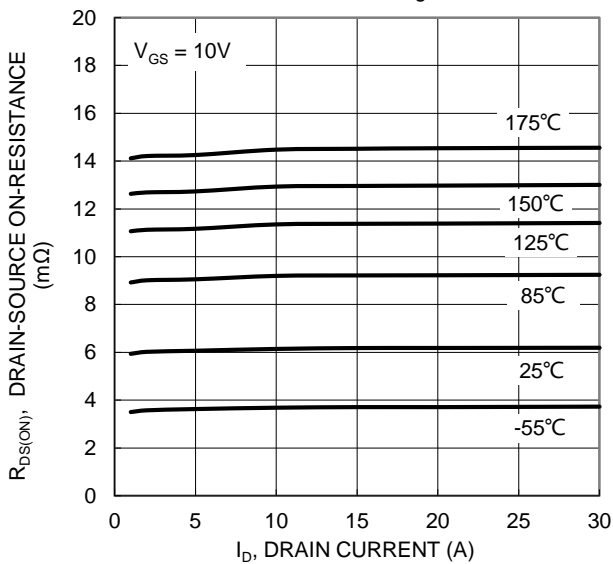


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

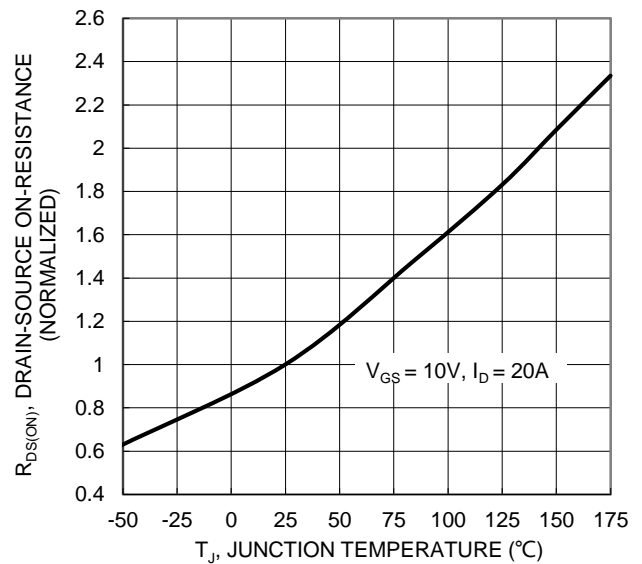


Figure 6. On-Resistance Variation with Temperature

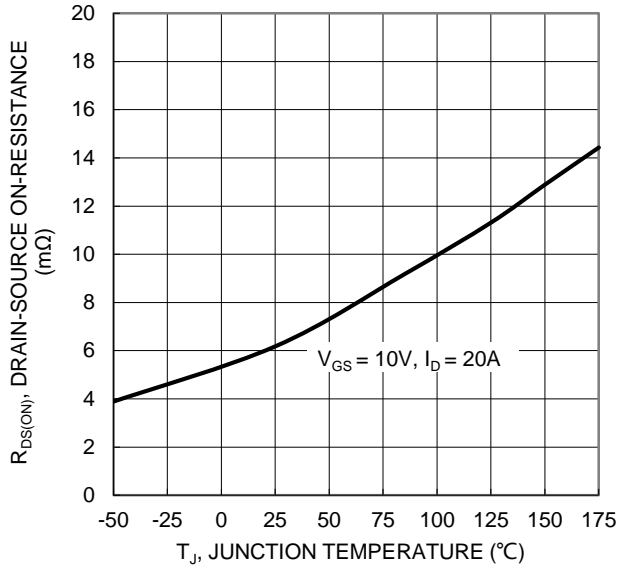


Figure 7. On-Resistance Variation with Temperature

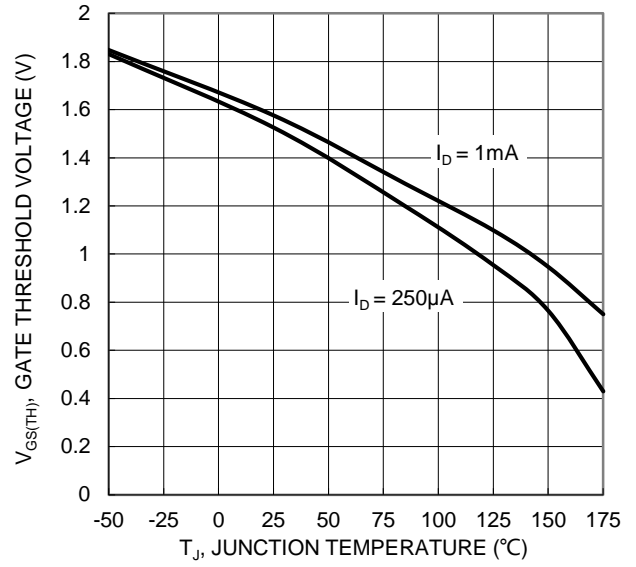


Figure 8. Gate Threshold Variation vs. Junction Temperature

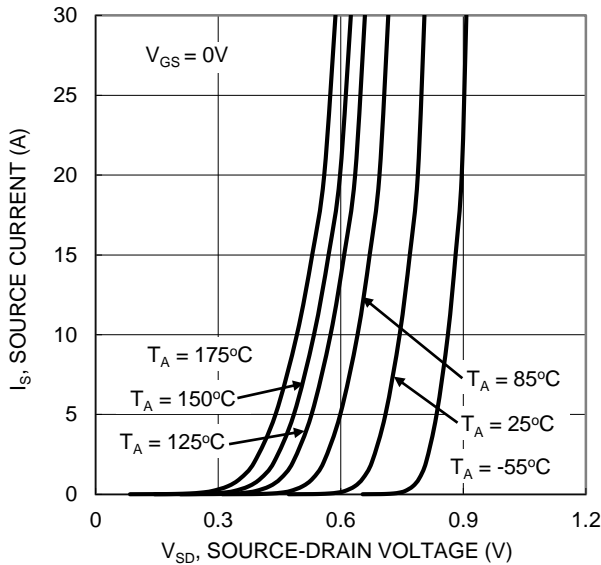


Figure 9. Diode Forward Voltage vs. Current

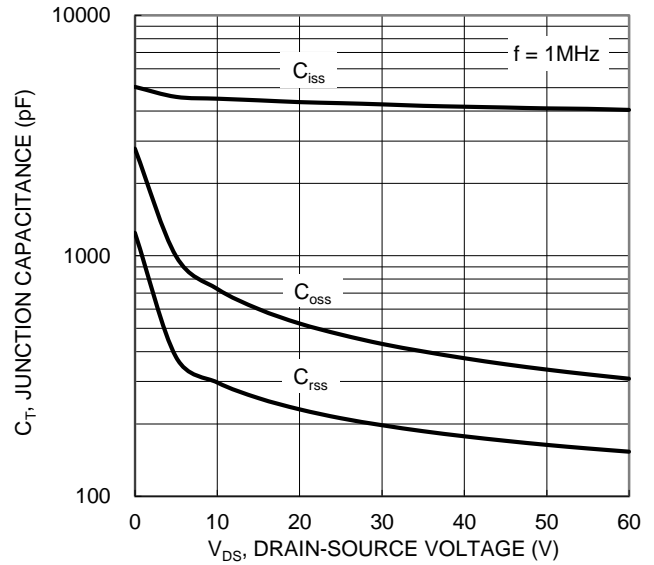


Figure 10. Typical Junction Capacitance

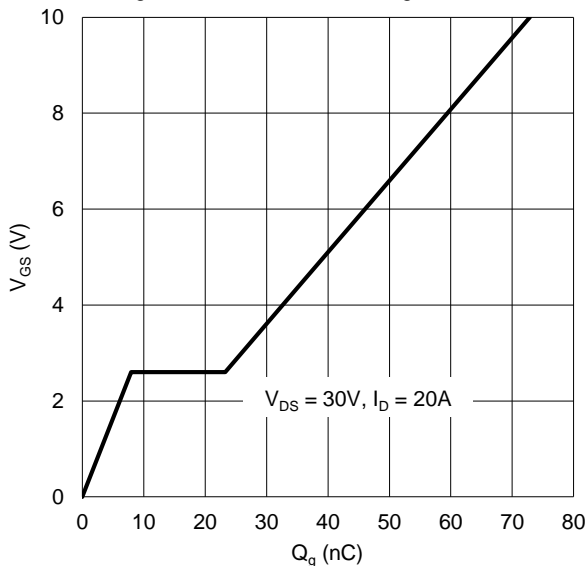


Figure 11. Gate Charge

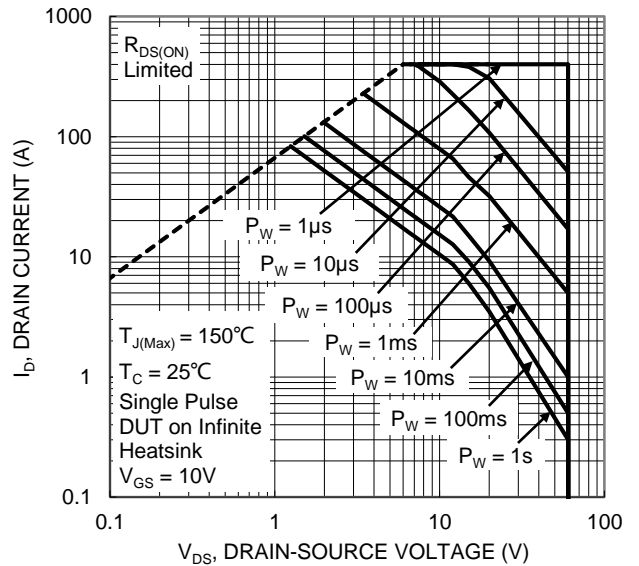


Figure 12. SOA, Safe Operation Area

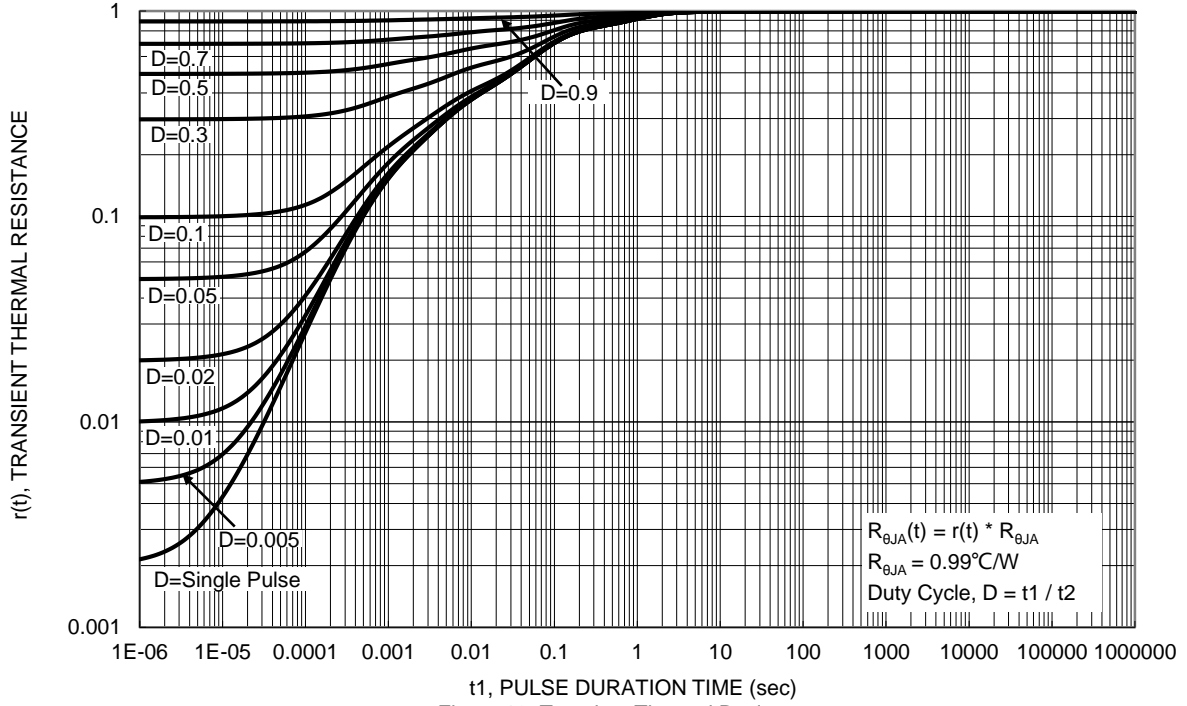
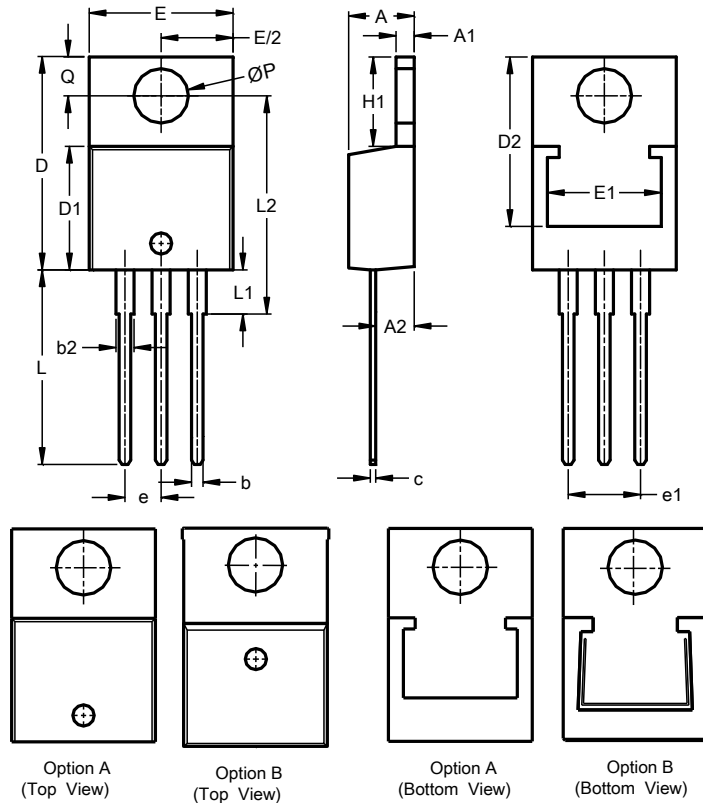


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO220AB (Generic)



TO220AB (Generic)			
Dim	Min	Max	Typ
A	3.56	4.82	-
A1	0.51	1.39	-
A2	2.04	2.92	-
b	0.39	1.01	0.81
b2	1.15	1.77	1.24
c	0.356	0.61	-
D	14.22	16.51	-
D1	8.39	9.01	-
D2	11.45	12.87	-
e	-	-	2.54
e1	-	-	5.08
E	9.66	10.66	-
E1	6.86	8.89	-
H1	5.85	6.85	-
L	12.70	14.73	-
L1	-	4.42	-
L2	15.80	17.51	16.00
P	3.54	4.08	-
Q	2.54	3.42	-
All Dimensions in mm			

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